

RGTVX2TS65DGC13

650V 60A Field Stop Trench IGBT

V_{CES}	650V
I_C (100°C)	60A
$V_{CE(sat)}$ (Typ.)	1.5V
P_D	319W

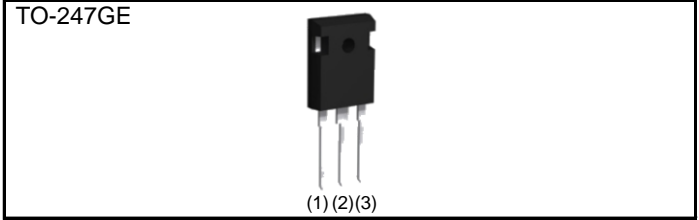
●Features

- 1) Low Collector - Emitter Saturation Voltage
- 2) High Speed Switching & Low Switching Loss
- 3) Short Circuit Withstand Time 2 μ s
- 4) Built in Very Fast & Soft Recovery FRD
- 5) Pb - free Lead Plating ; RoHS Compliant

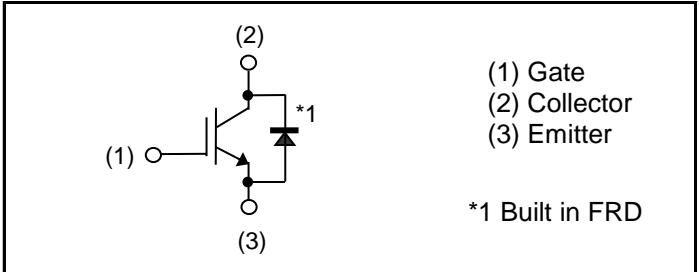
●Application

Solar Inverter
UPS
Welding
IH
PFC

●Outline



●Inner Circuit



●Packaging Specifications

Type	Packaging	Tube
	Reel Size (mm)	-
	Tape Width (mm)	-
	Basic Ordering Unit (pcs)	600
	Packing Code	C13
	Marking	RGTVX2TS65D

●Absolute Maximum Ratings (at $T_C = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit	
Collector - Emitter Voltage	V_{CES}	650	V	
Gate - Emitter Voltage	V_{GES}	± 30	V	
Collector Current	$T_C = 25^\circ\text{C}$	I_C	111	A
	$T_C = 100^\circ\text{C}$	I_C	60	A
Pulsed Collector Current	I_{CP}^{*1}	240	A	
Diode Forward Current	$T_C = 25^\circ\text{C}$	I_F	98	A
	$T_C = 100^\circ\text{C}$	I_F	60	A
Diode Pulsed Forward Current	I_{FP}^{*1}	240	A	
Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	319	W
	$T_C = 100^\circ\text{C}$	P_D	159	W
Operating Junction Temperature	T_j	-40 to +175	$^\circ\text{C}$	
Storage Temperature	T_{stg}	-55 to +175	$^\circ\text{C}$	

*1 Pulse width limited by T_{jmax} .

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●Thermal Resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	0.47	°C/W
Thermal Resistance Diode Junction - Case	$R_{\theta(j-c)}$	-	-	0.70	°C/W

●IGBT Electrical Characteristics (at $T_j = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Collector - Emitter Breakdown Voltage	BV_{CES}	$I_C = 10\mu\text{A}, V_{GE} = 0\text{V}$	650	-	-	V
Collector Cut - off Current	I_{CES}	$V_{CE} = 650\text{V}, V_{GE} = 0\text{V}$	-	-	10	μA
Gate - Emitter Leakage Current	I_{GES}	$V_{GE} = \pm 30\text{V}, V_{CE} = 0\text{V}$	-	-	± 200	nA
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE} = 5\text{V}, I_C = 41.9\text{mA}$	5.0	6.0	7.0	V
Collector - Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 60\text{A}, V_{GE} = 15\text{V},$ $T_j = 25^\circ\text{C}$	-	1.5	1.9	V
		$T_j = 175^\circ\text{C}$	-	1.85	-	

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●IGBT Electrical Characteristics (at $T_j = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input Capacitance	C_{ies}	$V_{CE} = 30\text{V}$,	-	3610	-	pF
Output Capacitance	C_{oes}	$V_{GE} = 0\text{V}$,	-	140	-	
Reverse transfer Capacitance	C_{res}	$f = 1\text{MHz}$	-	58	-	
Total Gate Charge	Q_g	$V_{CE} = 400\text{V}$,	-	123	-	nC
Gate - Emitter Charge	Q_{ge}	$I_C = 60\text{A}$,	-	22	-	
Gate - Collector Charge	Q_{gc}	$V_{GE} = 15\text{V}$	-	48	-	
Turn - on Delay Time	$t_{d(on)}$	$I_C = 60\text{A}$, $V_{CC} = 400\text{V}$, $V_{GE} = 15\text{V}$, $R_G = 10\Omega$, $T_j = 25^\circ\text{C}$ Inductive Load * E_{on} include diode reverse recovery	-	49	-	ns
Rise Time	t_r		-	23	-	
Turn - off Delay Time	$t_{d(off)}$		-	150	-	
Fall Time	t_f		-	34	-	
Turn - on Switching Loss	E_{on}		-	2.08	-	mJ
Turn - off Switching Loss	E_{off}		-	1.15	-	
Turn - on Delay Time	$t_{d(on)}$	$I_C = 60\text{A}$, $V_{CC} = 400\text{V}$, $V_{GE} = 15\text{V}$, $R_G = 10\Omega$, $T_j = 175^\circ\text{C}$ Inductive Load * E_{on} include diode reverse recovery	-	46	-	ns
Rise Time	t_r		-	28	-	
Turn - off Delay Time	$t_{d(off)}$		-	164	-	
Fall Time	t_f		-	79	-	
Turn - on Switching Loss	E_{on}		-	2.11	-	mJ
Turn - off Switching Loss	E_{off}		-	1.55	-	
Reverse Bias Safe Operating Area	RBSOA	$I_C = 240\text{A}$, $V_{CC} = 520\text{V}$, $V_P = 650\text{V}$, $V_{GE} = 15\text{V}$, $R_G = 100\Omega$, $T_j = 175^\circ\text{C}$	FULL SQUARE			-
Short Circuit Withstand Time	t_{sc}	$V_{CC} \leq 360\text{V}$, $V_{GE} = 15\text{V}$, $T_j = 25^\circ\text{C}$	2	-	-	μs

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●FRD Electrical Characteristics (at $T_j = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Diode Forward Voltage	V_F	$I_F = 60\text{A}$, $T_j = 25^\circ\text{C}$ $T_j = 175^\circ\text{C}$	-	1.45	1.9	V
			-	1.55	-	
Diode Reverse Recovery Time	t_{rr}	$I_F = 60\text{A}$, $V_{CC} = 400\text{V}$, $di_F/dt = 200\text{A}/\mu\text{s}$, $T_j = 25^\circ\text{C}$	-	111	-	ns
Diode Peak Reverse Recovery Current	I_{rr}		-	12.8	-	A
Diode Reverse Recovery Charge	Q_{rr}		-	0.86	-	μC
Diode Reverse Recovery Energy	E_{rr}		-	36.3	-	μJ
Diode Reverse Recovery Time	t_{rr}		-	197	-	ns
Diode Peak Reverse Recovery Current	I_{rr}	$I_F = 60\text{A}$, $V_{CC} = 400\text{V}$, $di_F/dt = 200\text{A}/\mu\text{s}$, $T_j = 175^\circ\text{C}$	-	16.6	-	A
Diode Reverse Recovery Charge	Q_{rr}		-	1.95	-	μC
Diode Reverse Recovery Energy	E_{rr}		-	126	-	μJ

●Electrical Characteristic Curves

Fig.1 Power Dissipation vs. Case Temperature

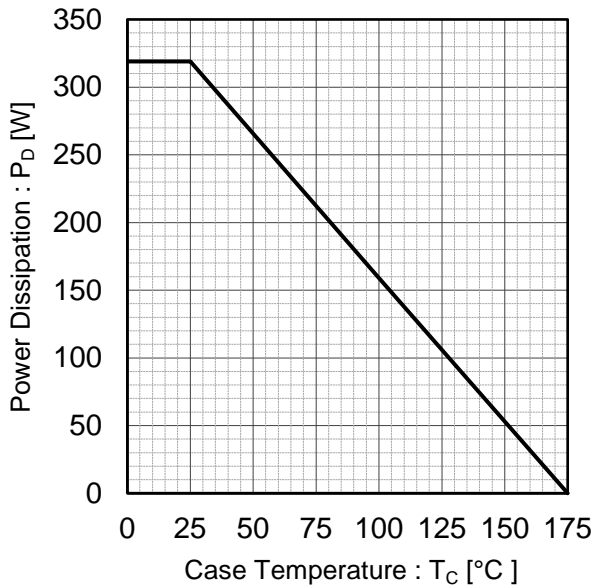


Fig.2 Collector Current vs. Case Temperature

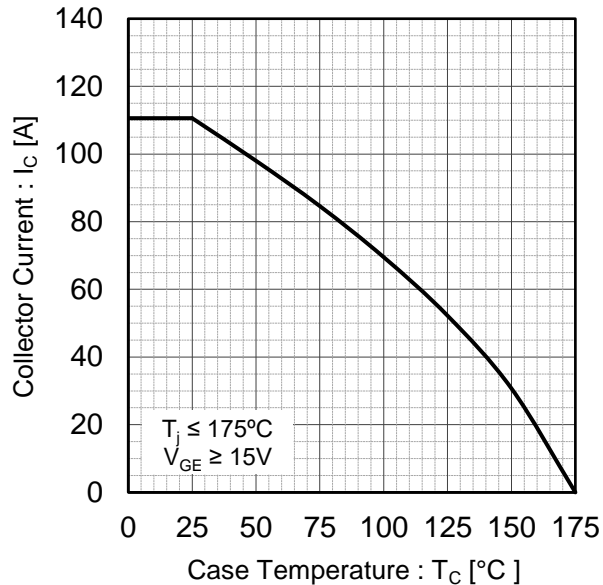


Fig.3 Forward Bias Safe Operating Area

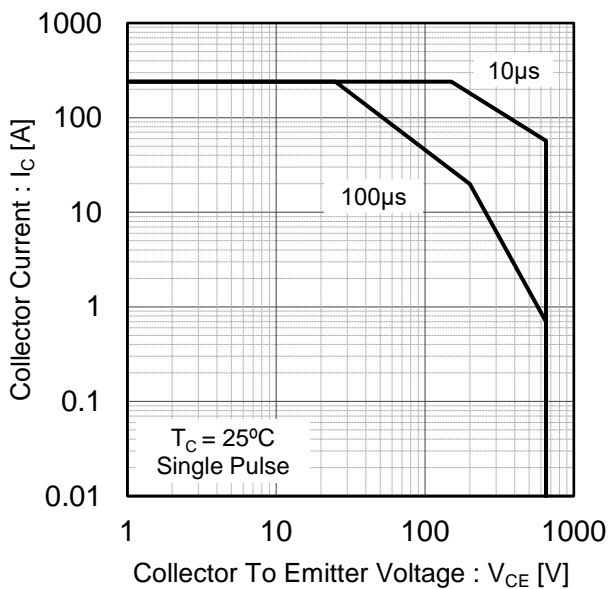
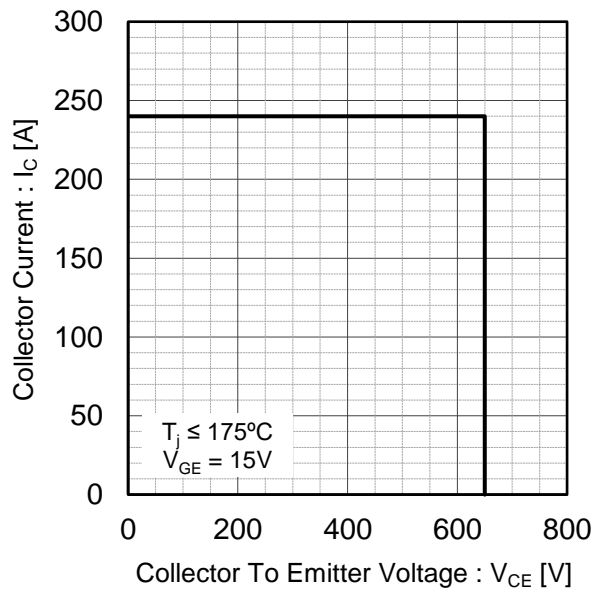


Fig.4 Reverse Bias Safe Operating Area



●Electrical Characteristic Curves

Fig.5 Typical Output Characteristics

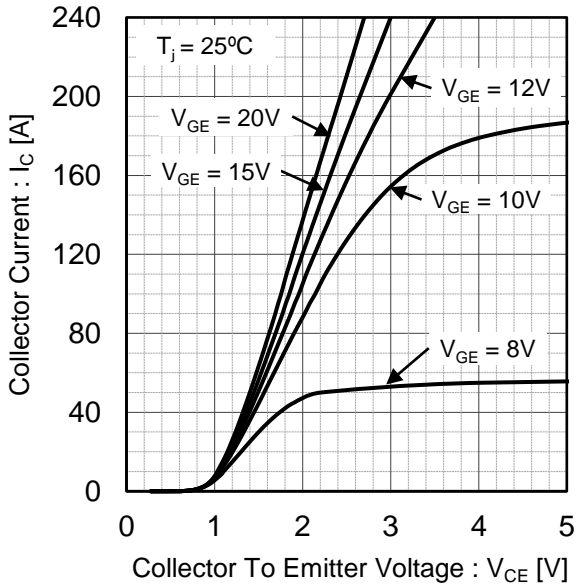


Fig.6 Typical Output Characteristics

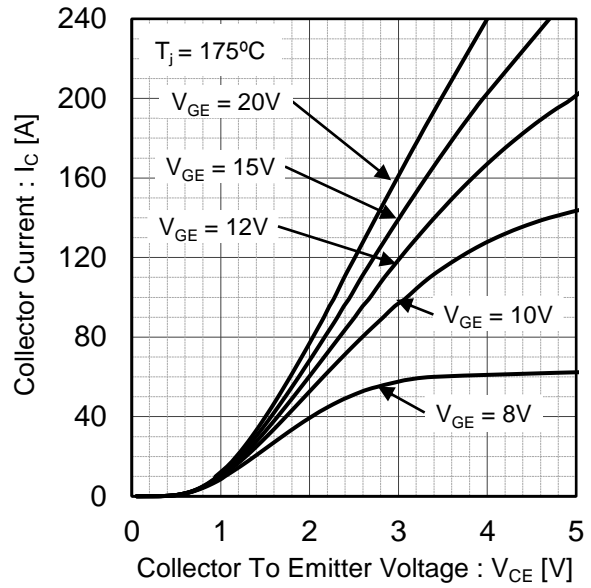


Fig.7 Typical Transfer Characteristics

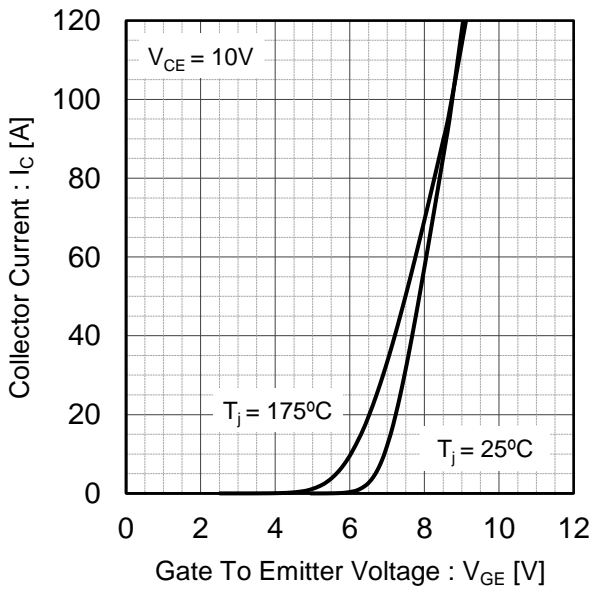
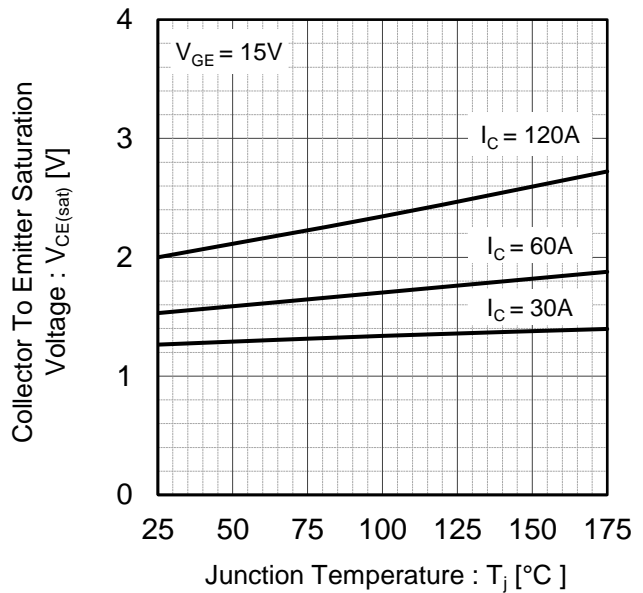


Fig.8 Typical Collector to Emitter Saturation Voltage vs. Junction Temperature



●Electrical Characteristic Curves

Fig.9 Typical Collector to Emitter Saturation Voltage vs. Gate to Emitter Voltage

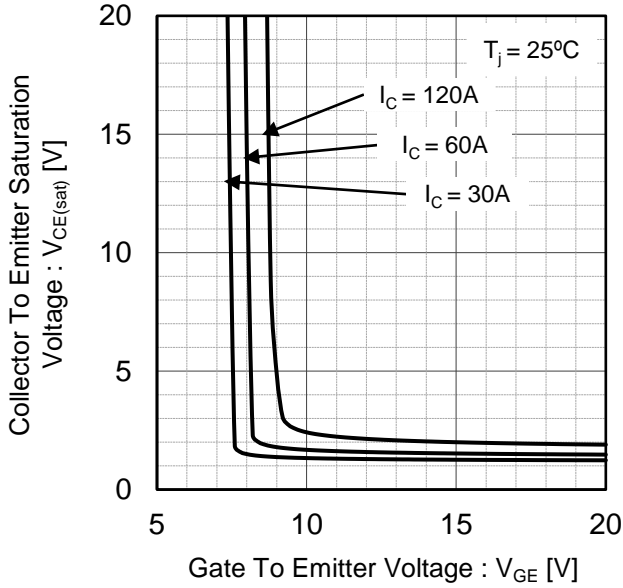


Fig.10 Typical Collector to Emitter Saturation Voltage vs. Gate to Emitter Voltage

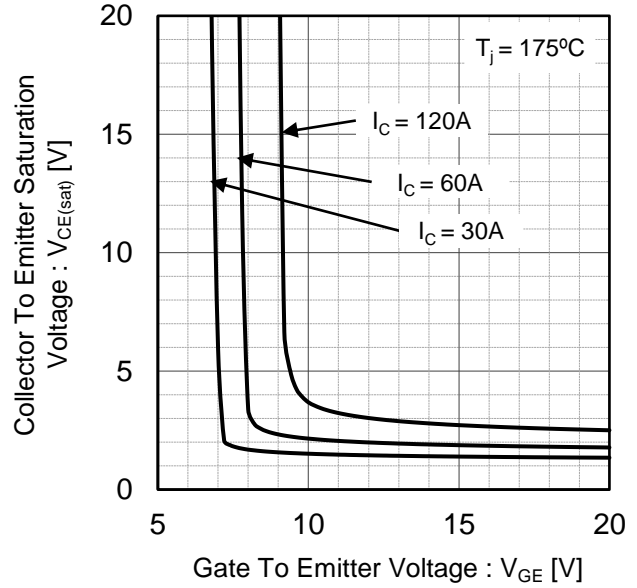


Fig.11 Typical Switching Time vs. Collector Current

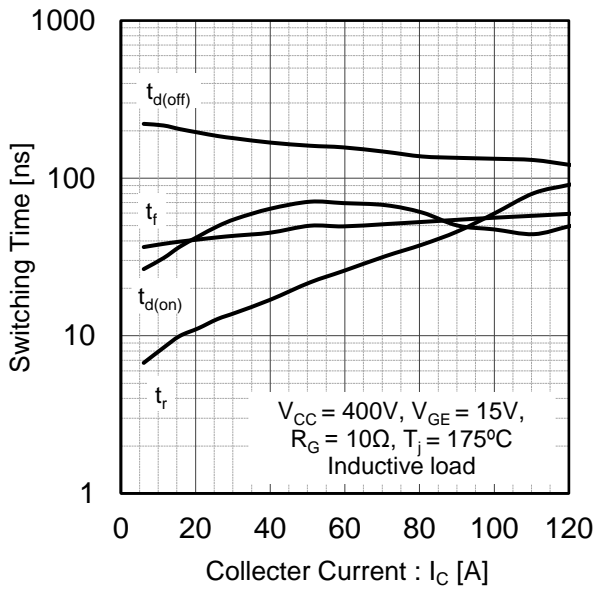
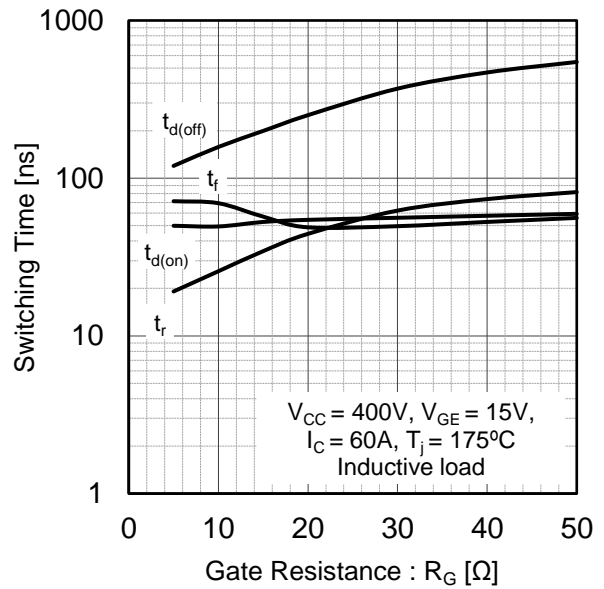


Fig.12 Typical Switching Time vs. Gate Resistance



●Electrical Characteristic Curves

Fig.13 Typical Switching Energy Losses vs. Collector Current

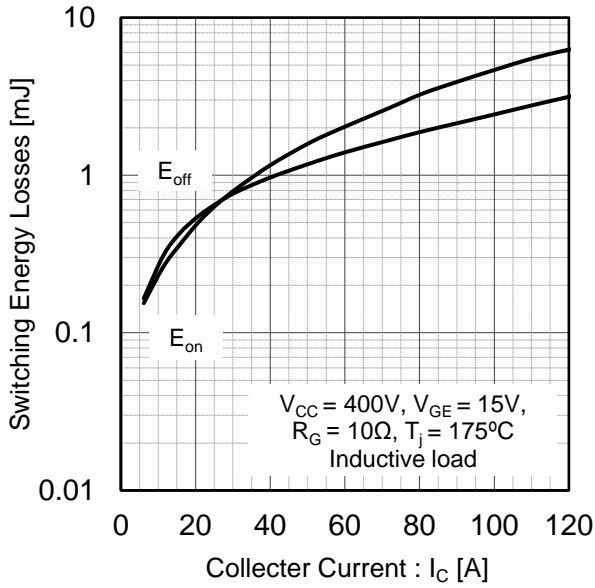


Fig.14 Typical Switching Energy Losses vs. Gate Resistance

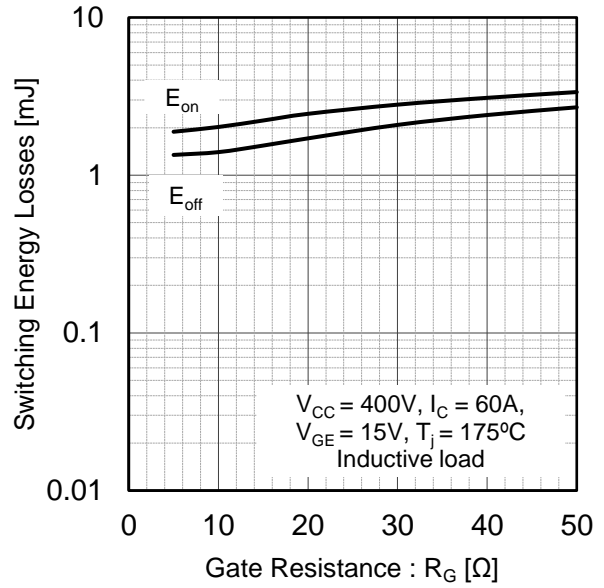


Fig.15 Typical Capacitance vs. Collector to Emitter Voltage

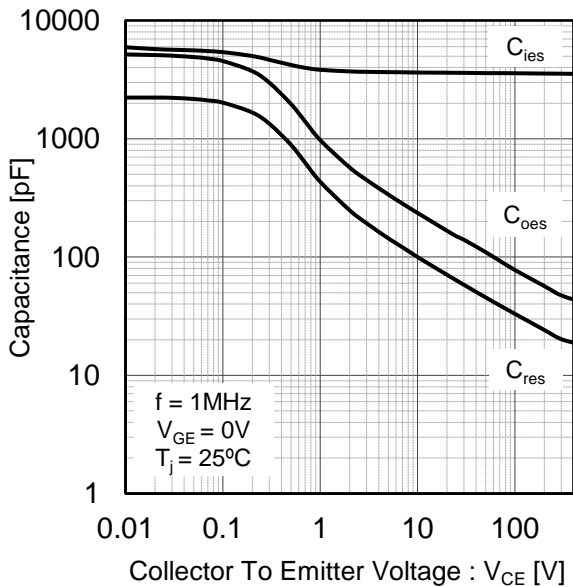
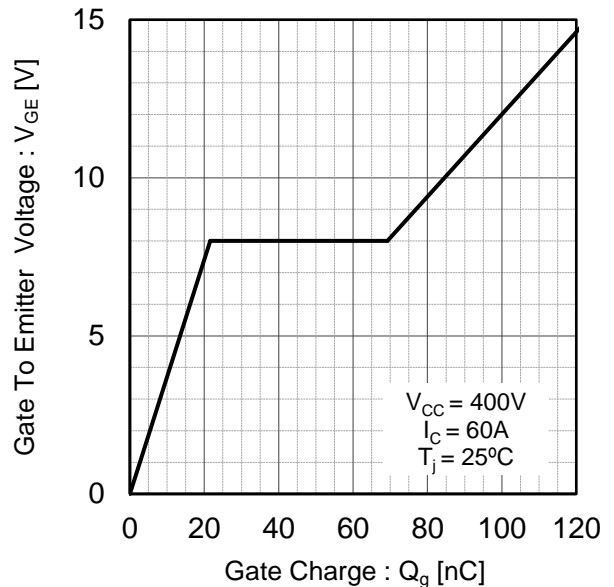


Fig.16 Typical Gate Charge



●Electrical Characteristic Curves

Fig.17 Typical Diode Forward Current vs. Forward Voltage

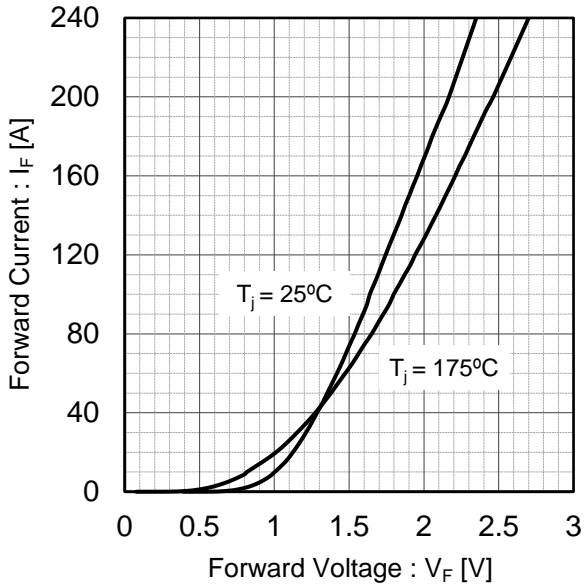


Fig.18 Typical Diode Reverse Recovery Time vs. Forward Current

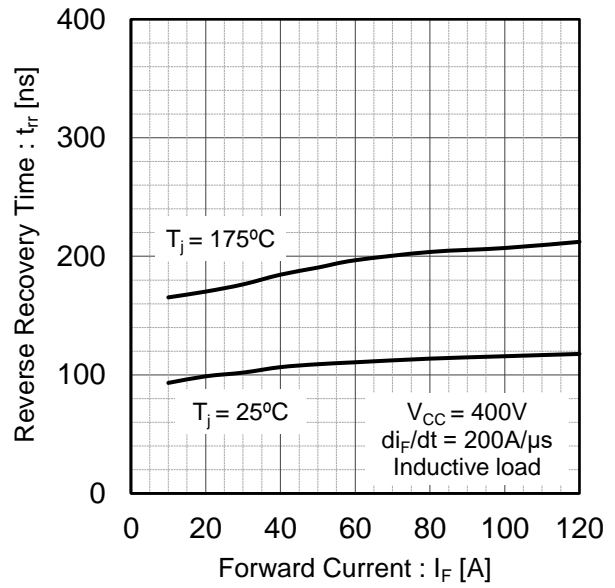


Fig.19 Typical Diode Reverse Recovery Current vs. Forward Current

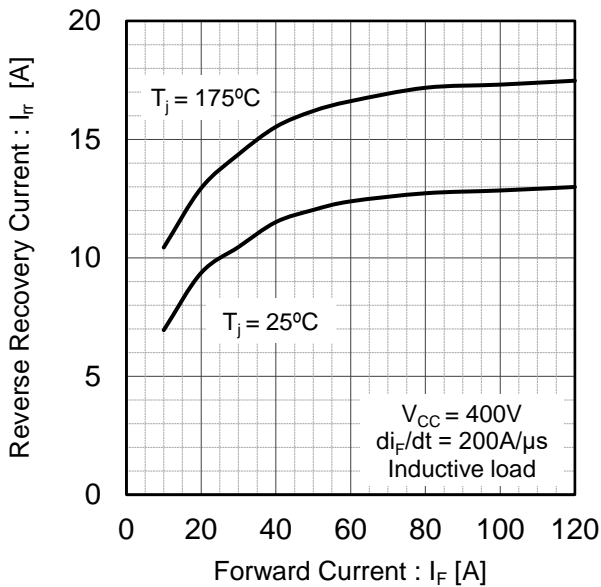
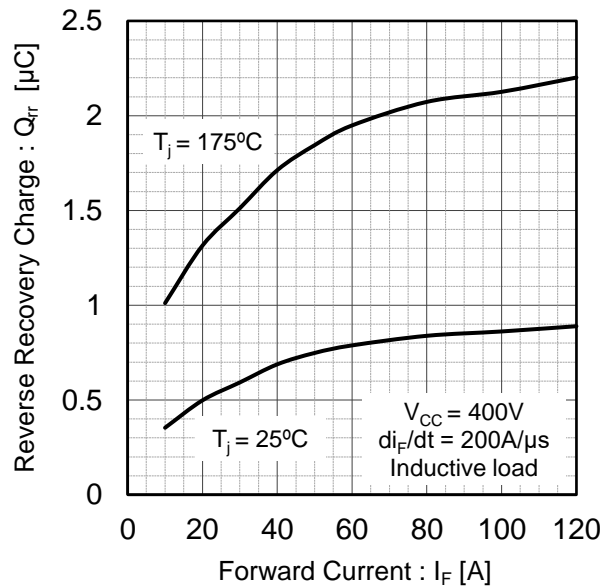


Fig.20 Typical Diode Reverse Recovery Charge vs. Forward Current



●Electrical Characteristic Curves

Fig.21 Typical IGBT Transient Thermal Impedance

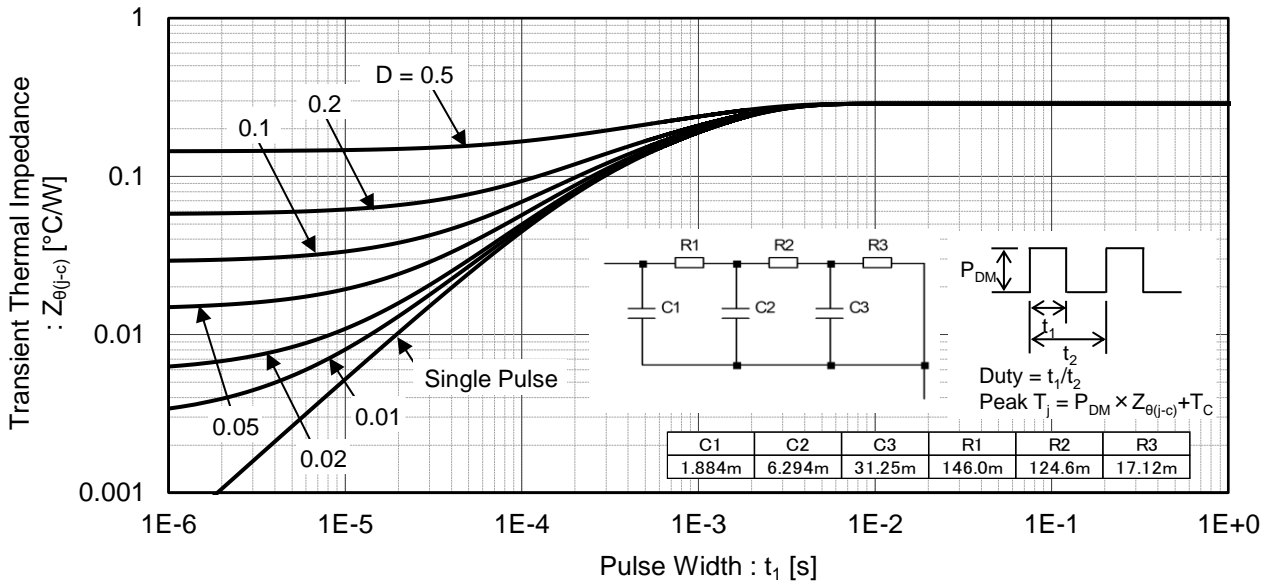
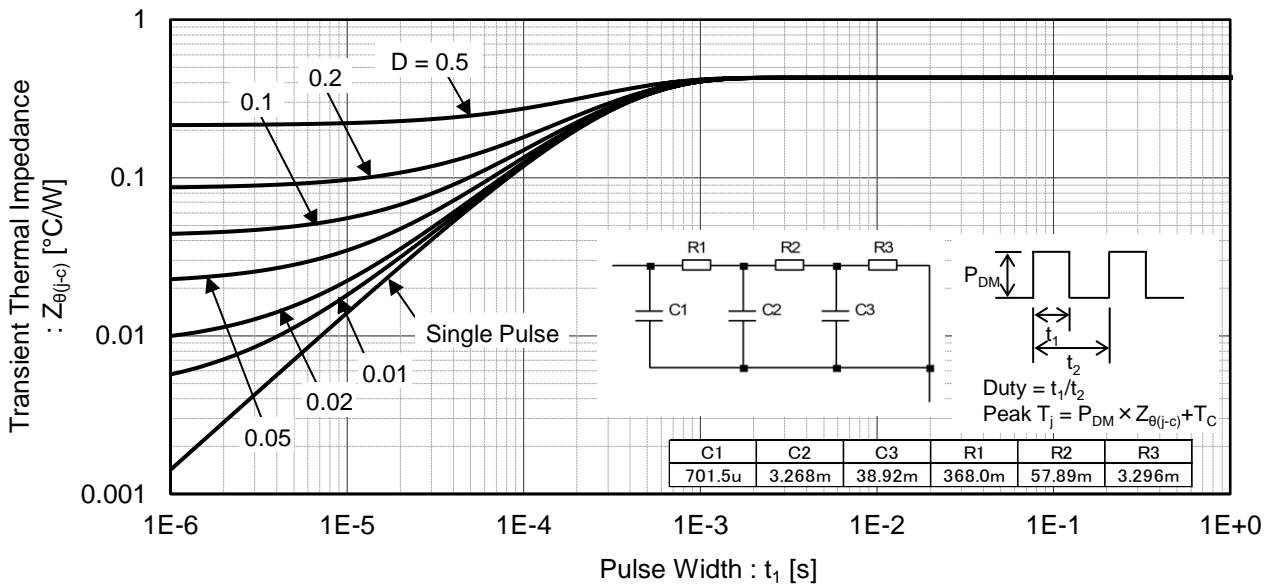


Fig.22 Typical Diode Transient Thermal Impedance



● Inductive Load Switching Circuit and Waveform

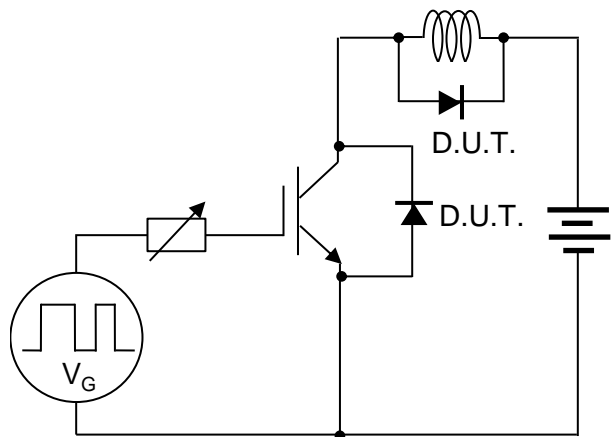


Fig.23 Inductive Load Circuit

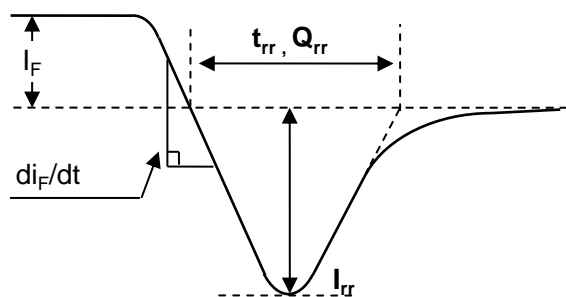


Fig.25 Diode Reverse Recovery Waveform

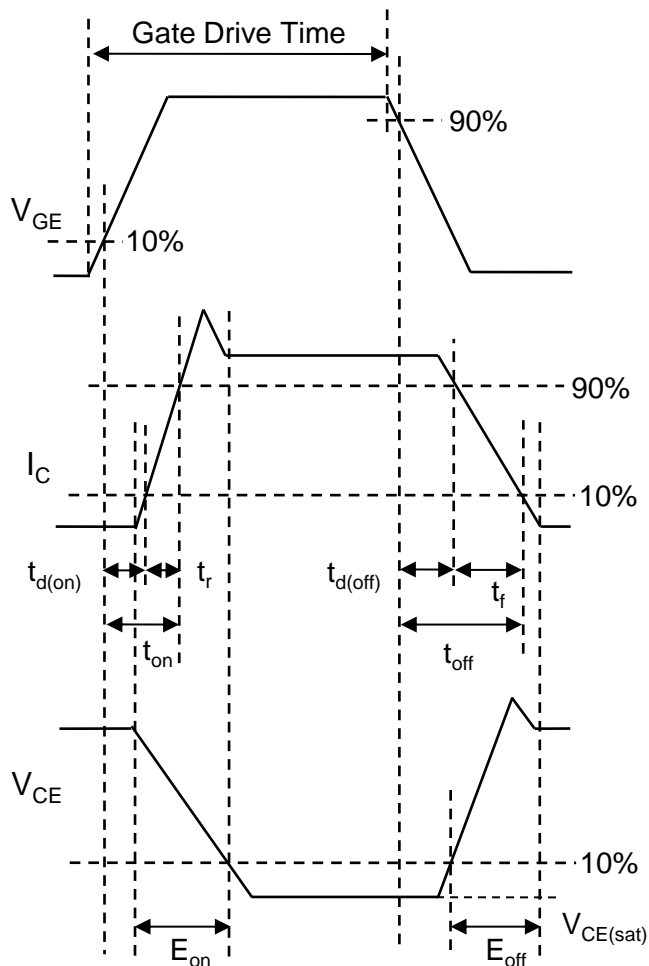


Fig.24 Inductive Load Waveform